



	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	2358	(non-porous\$2 or (non adj porous\$2)) near15 (silicon or wafer\$1 or substrate or semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 16:57			0
2	BRS	L2	196701	(porous\$2 or hole\$1 or bubb1\$3 or void\$1 or cavit\$3) near15 (silicon or wafer\$1 or substrate or semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 18:09			0
3	BRS	L3	5165	(non-porous\$2 or (non adj porous\$2) or impermeabl\$3) near15 (silicon or wafer\$1 or substrate or semiconductor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 16:57			0
4	BRS	L4	3109	2 and 3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 16:56			0
5	BRS	L5	385	(non-porous\$2 or (non adj porous\$2)) near5 silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 16:58			0
6	BRS	L6	6924	porous\$2 near5 silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 16:59			0
7	BRS	L7	378	5 and 6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 16:59			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
8 BRS	L8	34995	(thick\$3 near10 (oxide\$1 or dioxide\$1 or dielectric\$1 or insulat\$3 or isolat\$3)) and (thin\$4 near10 (oxide\$1 or dioxide\$1 or dielectric\$1 or insulat\$3 or isolat\$3))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 17:03			0
9 BRS	L9	54	7 and 8	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 17:03			0
10 BRS	L10	465504	(multiple or differen\$3 or various or vary or varies or varying or two or second or another) near8 (oxide\$1 or dioxide\$1 or dielectric\$1 or insulat\$4 or isolat\$4)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 17:29			0
11 BRS	L11	180117	(first near8 (oxide\$1 or dioxide\$1 or dielectric\$1 or insulat\$4 or isolat\$4)) and (second near8 (oxide\$1 or dioxide\$1 or dielectric\$1 or insulat\$4 or isolat\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 17:31			0
12 BRS	L12	180117	(first near8 (oxide\$1 or dioxide\$1 or dielectric\$1 or insulat\$4 or isolat\$4)) and ((second or another) near8 (oxide\$1 or dioxide\$1 or dielectric\$1 or insulat\$4 or isolat\$4))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 17:34			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
13	BRS	L13	15690	(first near8 (oxide\$1 or dioxide\$1 or dielectric\$1 or insulat\$4 or isolat\$4)) with ((second or another) near8 (oxide\$1 or dioxide\$1 or dielectric\$1 or insulat\$4 or isolat\$4)) with (thicker or thinner or thinner or greater or smaller or less or bigger or more)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 17:37			0
14	BRS	L14	18632	(oxide\$1 or dioxide\$1 or dielectric or insulat\$4) with (varying or variable or varies or vary or differen\$4 or multiple) with (thickness\$2 or thick-ness\$2 or (thick adj ness))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 17:39			0
15	BRS	L15	6307	first with second with (thickness\$2 or thick-ness\$2 or (thick adj ness\$2)) with (oxide\$1 or dioxide\$1 or dielectric\$1 or insulat\$4) with (smaller or thinner or thin\$4 or thick\$3 or greater or less or more or bigger)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 17:41			0
16	BRS	L16	478508	8 or 10 or 11 or 12 or 13 or 14 or 15	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 17:47			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
17	BRS	L17	190	(convert\$3 or chang\$3 or produc\$4 or adapt\$3 or alter\$3 or renovat\$3 or switch\$3 or translat\$3 or form\$4) with 5 with 6	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 18:30			0
18	BRS	L18	82	16 and 17	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 17:59			0
19	BRS	L19	610069	(porous\$2 or hole\$1 or bubbl\$3 or void\$1 or cavit\$3 or vacanc\$3 or permeabl\$3) near15 (silicon or wafer\$1 or substrate or semiconductor or material\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 18:13			0
20	BRS	L20	43497	(non-porous\$2 or (non adj porous\$2) or impermeabl\$3 or porous-free or (free near2 porous\$2) or non-hole\$1 or (free near2 hole\$1) or non-bubbl\$3 or (free near2 bubbl\$3) or non-void\$1 or (void near2 free) or non-cavit\$3 or (free near2 cavit\$3) or non-vacanc\$3 or (free near2 vacanc\$3)) near15 (silicon or wafer\$1 or substrate or semiconductor or material\$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 18:20			0

Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
21	BRS	L21 8857	(convert\$3 or chang\$3 or produc\$4 or adapt\$3 or alter\$3 or renovat\$3 or switch\$3 or translat\$3 or form\$4) with (non-porous\$2 or (non adj porous\$2) or impermeabl\$3 or porous-free or (free near2 porous\$2) or non-hole\$1 or (free near2 hole\$1) or non-bubbl\$3 or (free near2 bubbl\$3) or non-void\$1 or (void near2 free) or non-cavit\$3 or (free near2 cavit\$3) or non-vacanc\$3 or (free near2 vacanc\$3)) with (silicon or wafer\$1 or substrate or semiconductor or material\$1) with (porous\$2 or hole\$1 or bubbl\$3 or void\$1 or cavit\$3 or vacanc\$3 or permeabl\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 18:27			0
22	BRS	L22 27879	19 and 20	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 18:27			0
23	BRS	L23 7654	(convert\$3 or chang\$3 or produc\$4 or adapt\$3 or alter\$3 or renovat\$3 or switch\$3 or translat\$3 or form\$4) with 19 with 20	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 18:34			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
24	BRS	L24	1185	23 and 16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 18:36			0
25	BRS	L25	1297	21 and 16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 18:37			0
26	BRS	L26	1297	24 or 25	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 18:39			0
27	BRS	L27	49	(gate adj oxide\$1) and 26	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 18:40			0
28	BRS	L28	130	(increas\$4 or boost\$4 or enlarg\$4 or rais\$4 or enhanc\$4 or high\$4 or bigger or great\$3) with (oxidiz\$8 or oxidat\$5) with (rates or rate or rat\$3) with 19	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 19:06			0
29	BRS	L29	52	28 and 16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 18:54			0

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
30	BRS	L30	5	(increas\$4 or boost\$4 or enlarg\$4 or rais\$4 or enhanc\$4 or high\$4 or bigger or great\$3) with (oxidiz\$8 or oxidat\$5) with (rates or rate or rat\$3) with 19 with 20	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 19:01			0
31	BRS	L31	36	(increas\$4 or boost\$4 or enlarg\$4 or rais\$4 or enhanc\$4 or high\$4 or bigger or great\$3) with (oxidiz\$8 or oxidat\$5) with 19 with 20	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 19:02			0
32	BRS	L32	36	(increas\$4 or boost\$4 or enlarg\$4 or rais\$4 or enhanc\$4 or high\$4 or bigger or great\$3) with (oxidiz\$8 or oxidat\$5) with 19 with 20	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 19:07			0
33	BRS	L33	1502	(increas\$4 or boost\$4 or enlarg\$4 or rais\$4 or enhanc\$4 or high\$4 or bigger or great\$3) with (oxidiz\$8 or oxidat\$5) with (19 or 20)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 19:10			0
34	BRS	L34	484	33 and 16	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/03/31 19:10			0